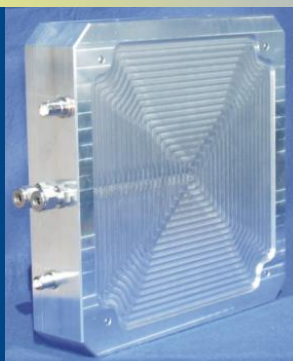


Diagnostics for Machine Protection at FERMI@Elettra



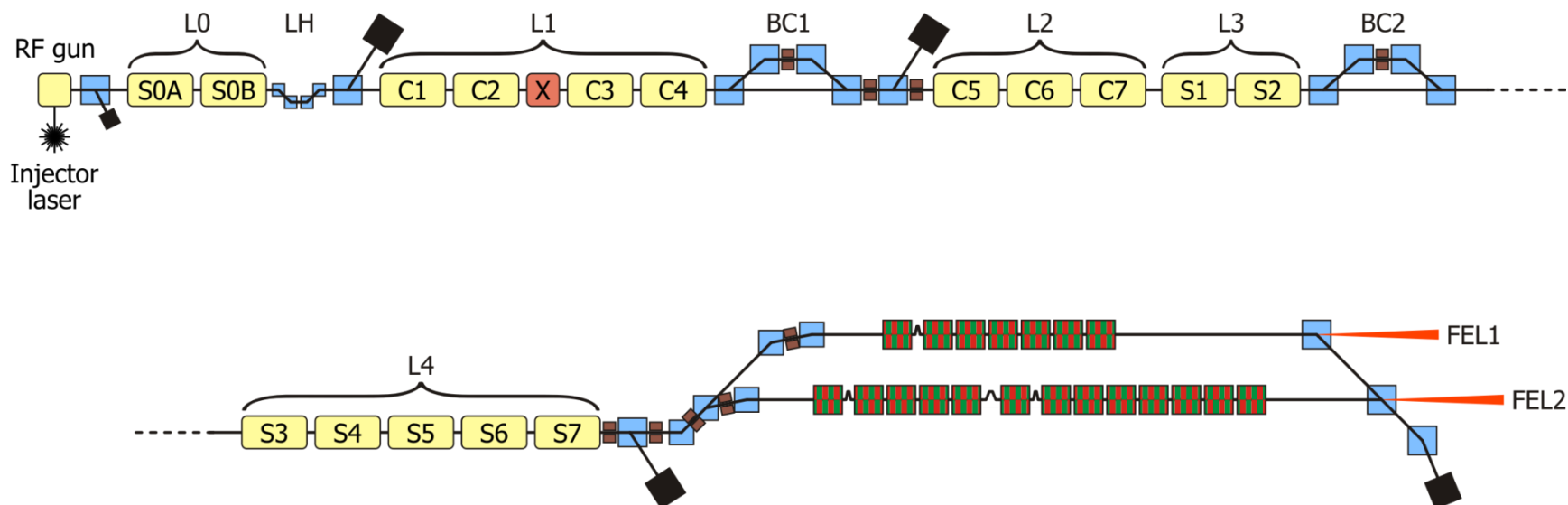
L. Fröhlich, A. I. Bogani, K. Casarin, G. Cautero, G. Gaio,
 F. Giacuzzo, D. Giuressi, A. Gubertini, R. H. Menk, E. Quai,
 G. Scalamera, A. Vascotto (Sincrotrone Trieste, Basovizza, Italy)
 L. Catani (INFN, Rome, Italy), D. Di Giovenale

- FERMI@Elettra
- MPS architecture
- General features

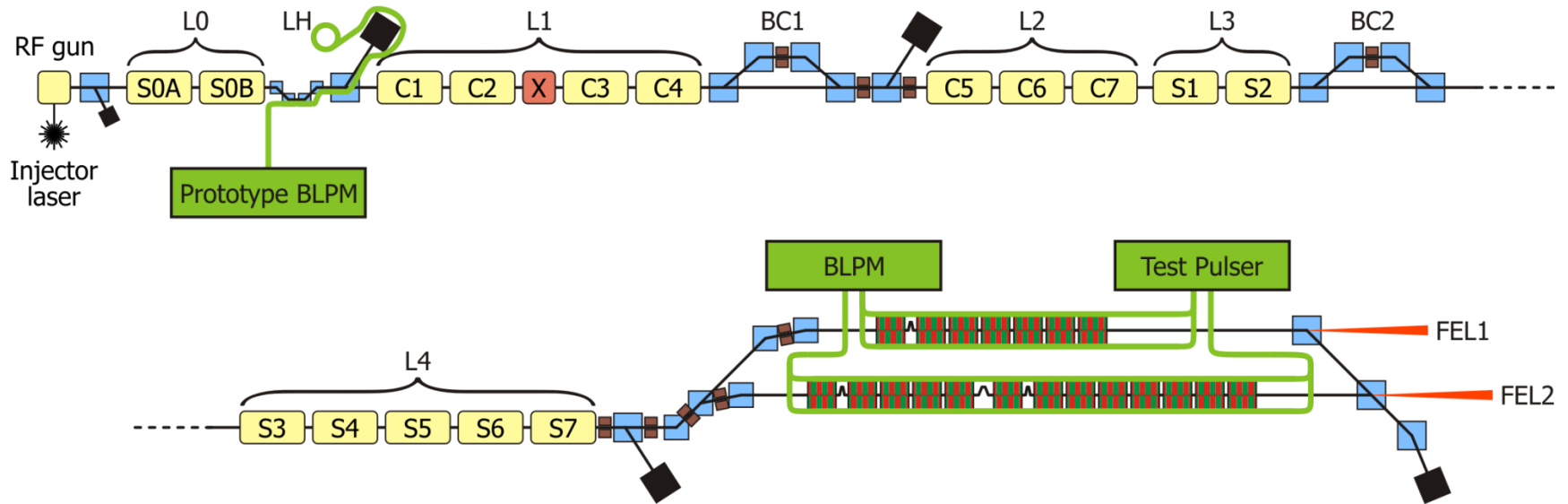
- Subsystems:
 - Fiber beam loss position monitors
 - Ionization chambers
 - RADFET online dosimetry



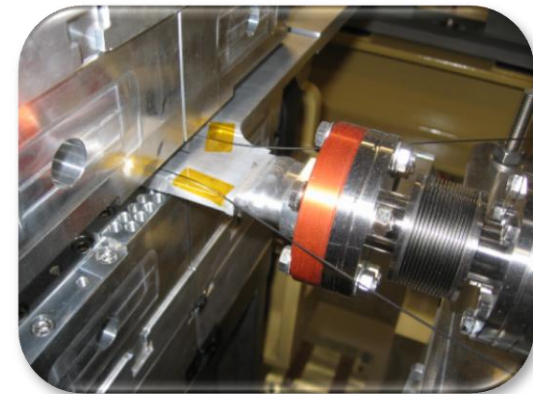


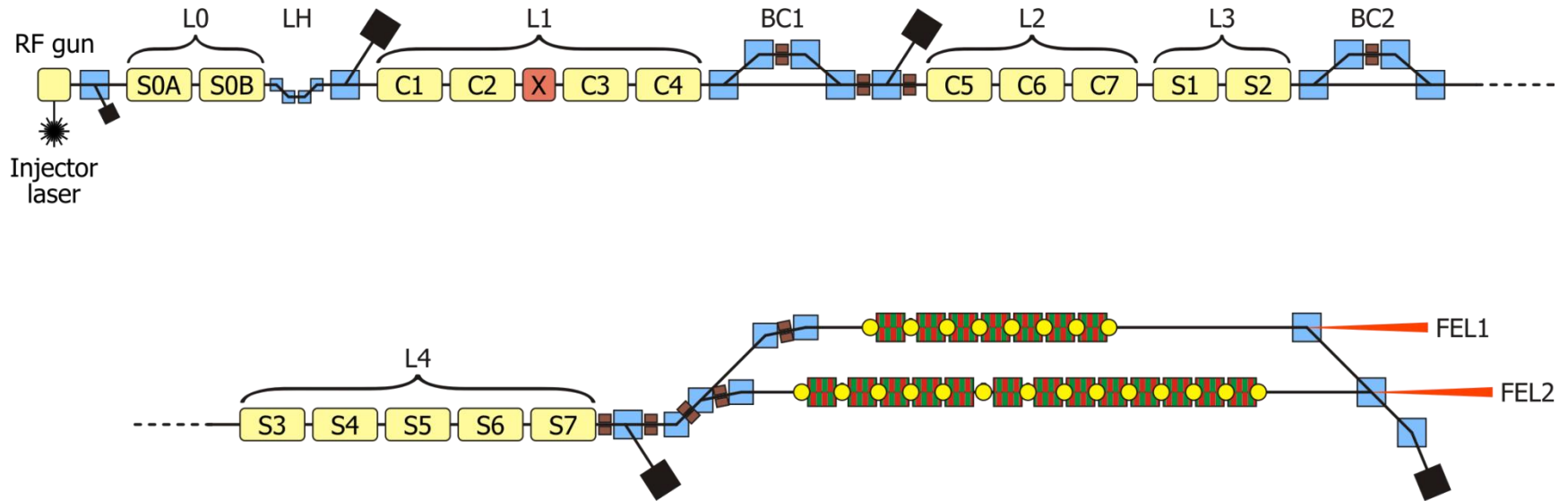


	Energy	Bunch Charge	Repetition Rate	Beam Power
Typical	1.2 GeV	350 pC	10 Hz	4.2 W
Design	1.5 GeV	1 nC	50 Hz	75 W

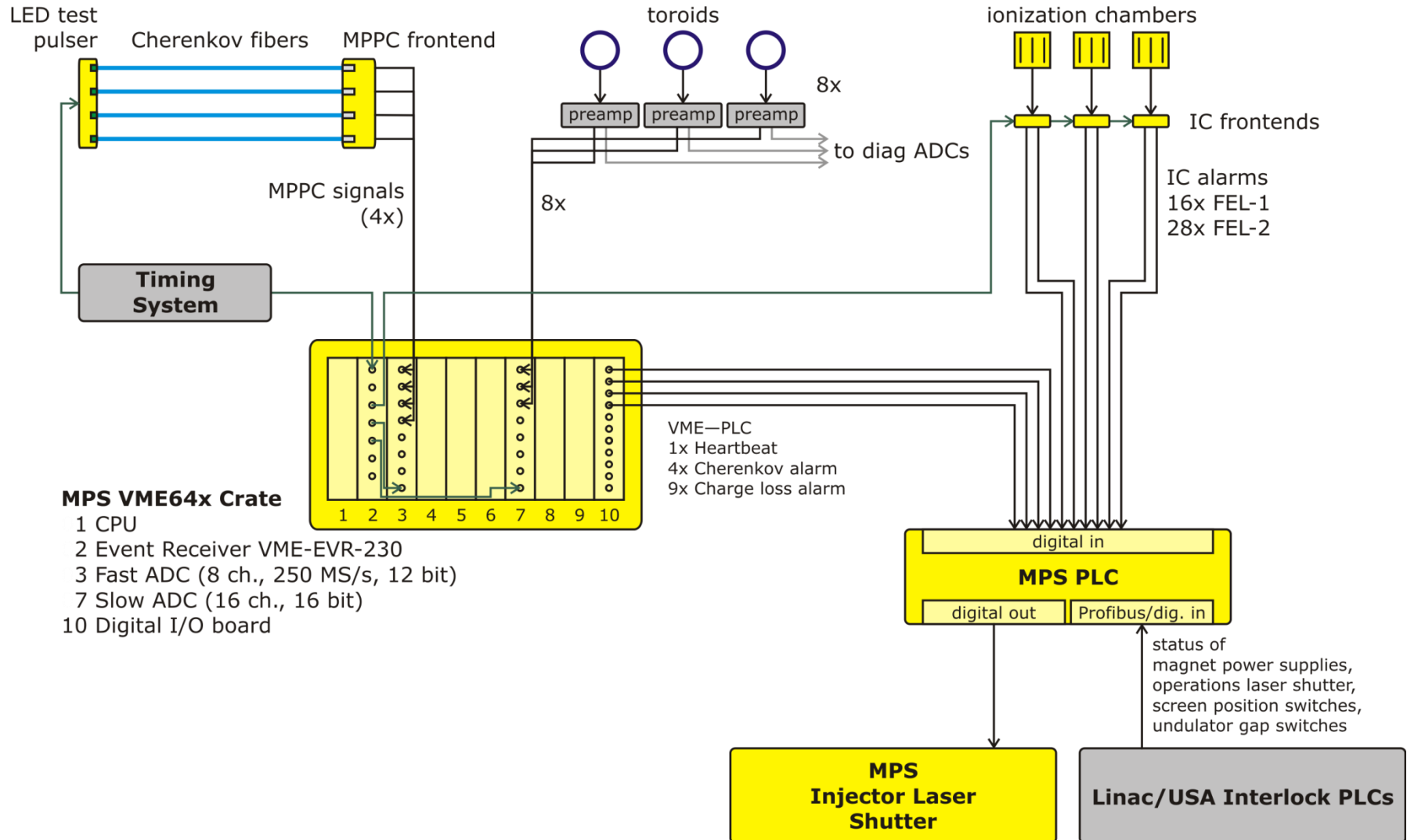


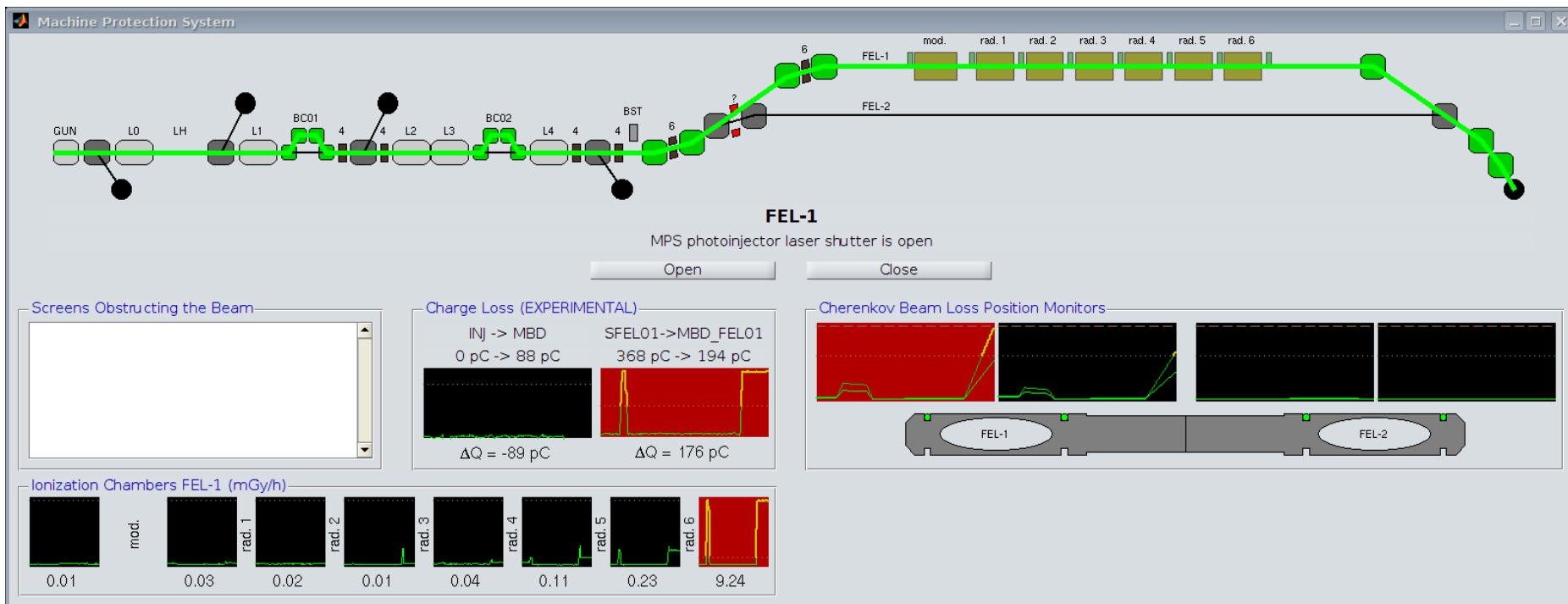
Cherenkov Fiber Beam Loss Position Monitors (BLPMs)





Ionization Chamber Beam Loss Monitors (BLMs)

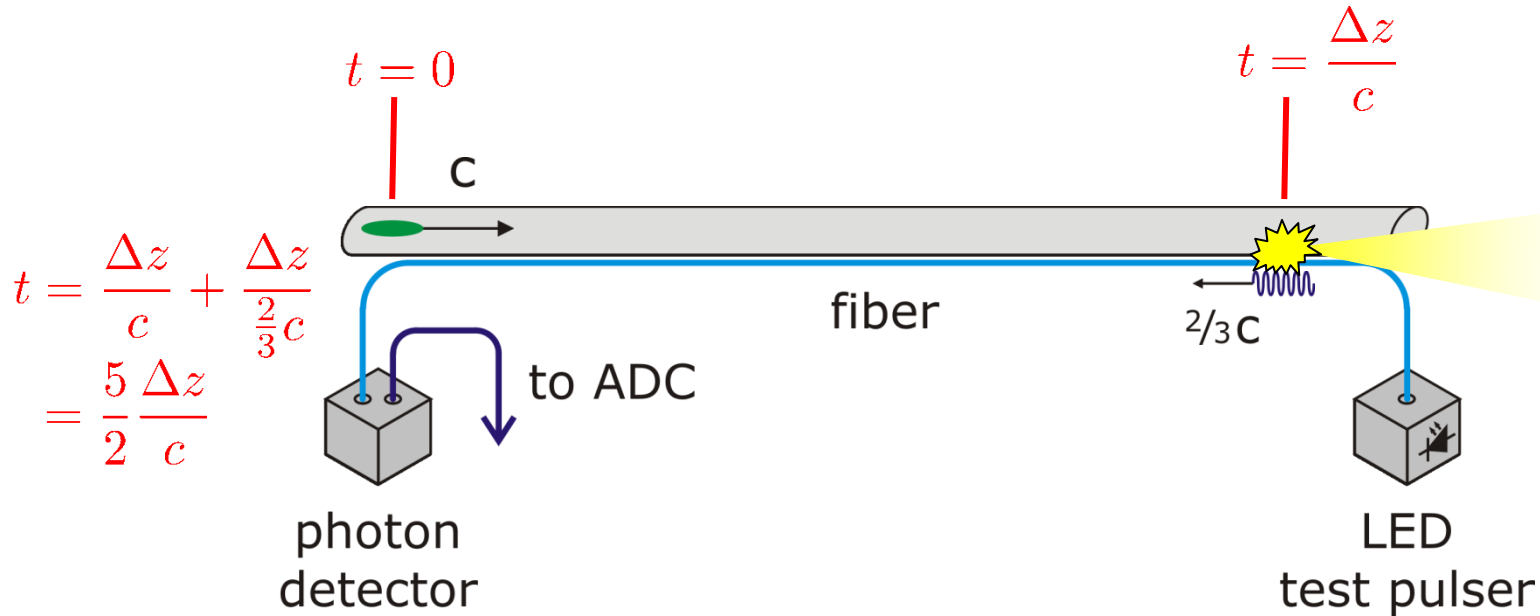




Cherenkov Fiber Beam Loss Position Monitor

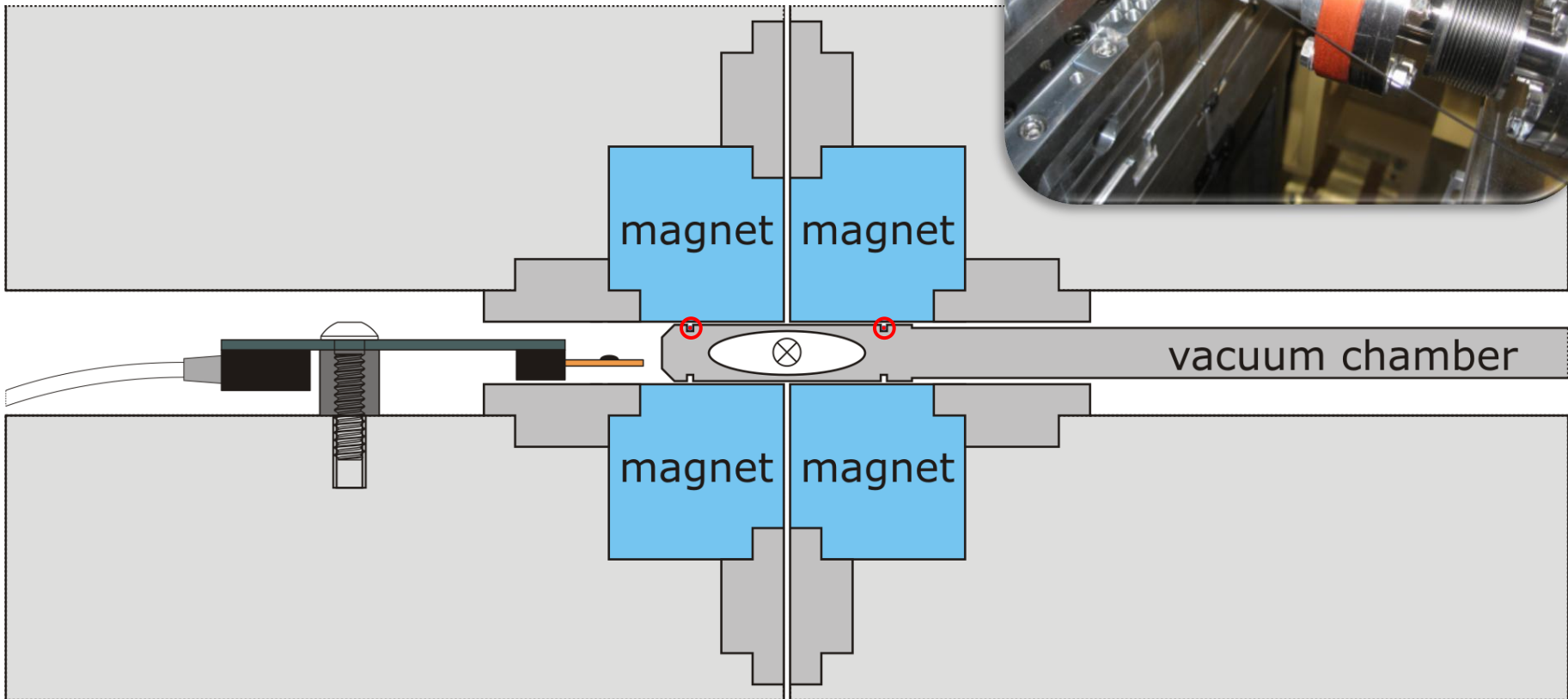
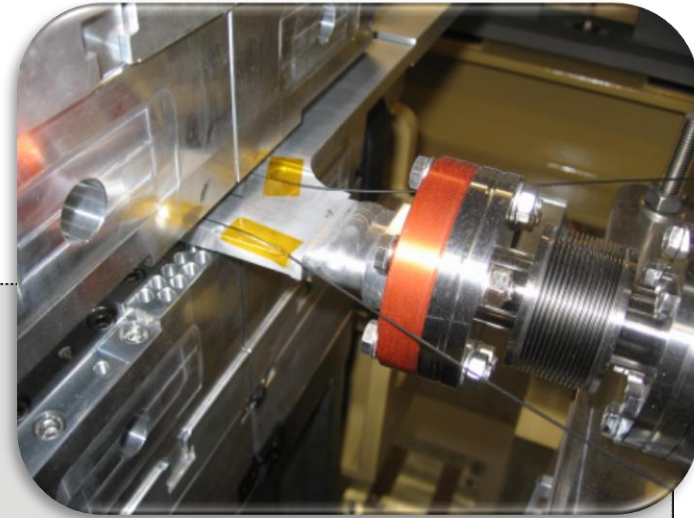
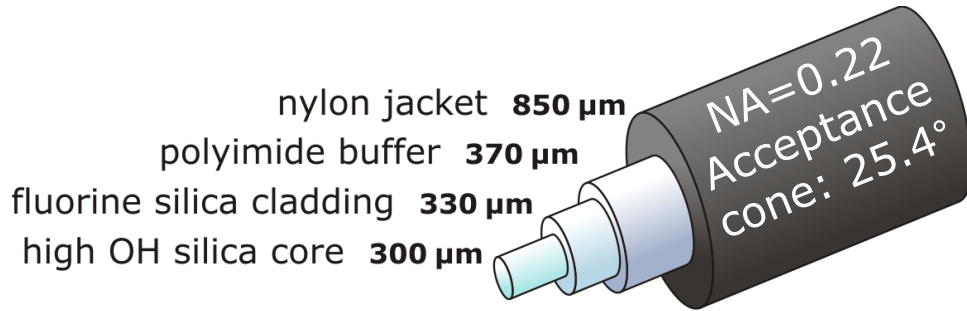
More information:

D. Di Giovenale, L. Catani, L. Fröhlich, "A read-out system for online monitoring of intensity and position of beam losses in electron linacs", Nucl. Instr. & Meth. A 665, pp. 33-39, 2011.

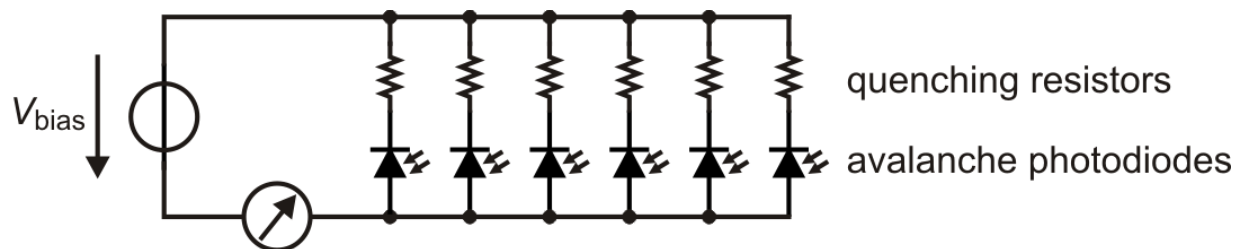
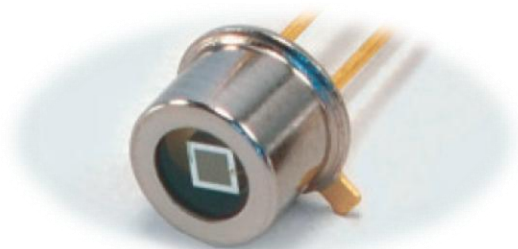
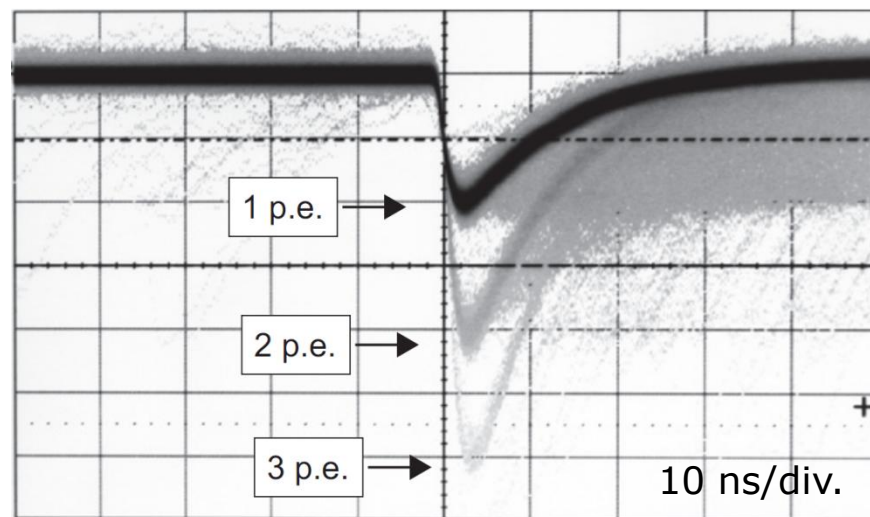


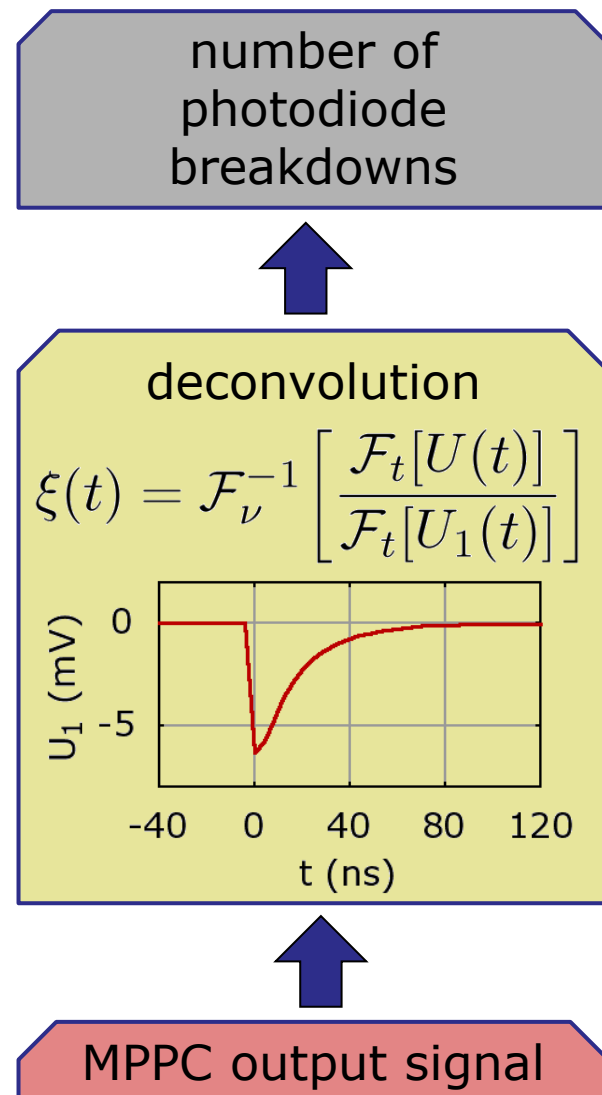
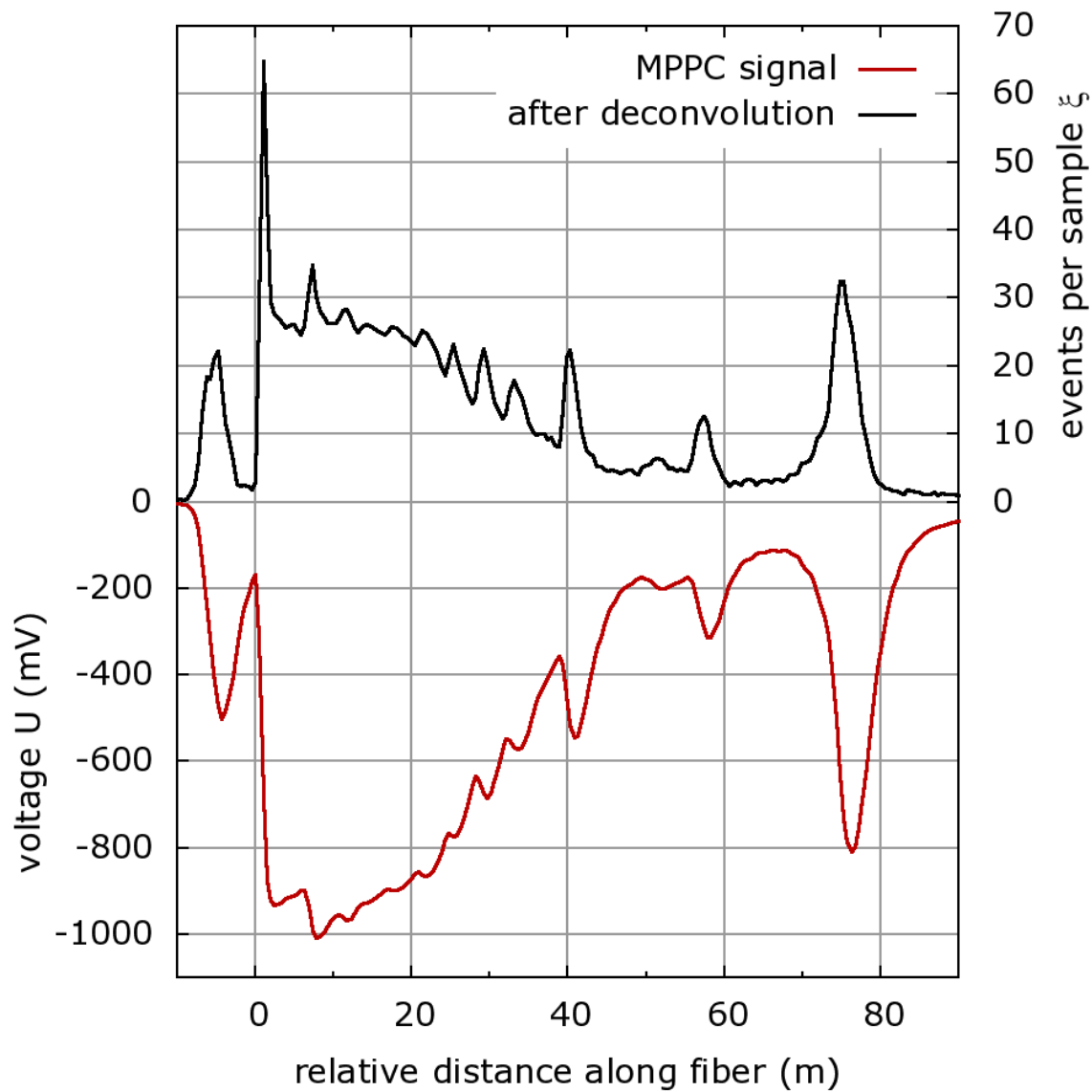
250 MS/s ADC → longitudinal resolution ~50 cm

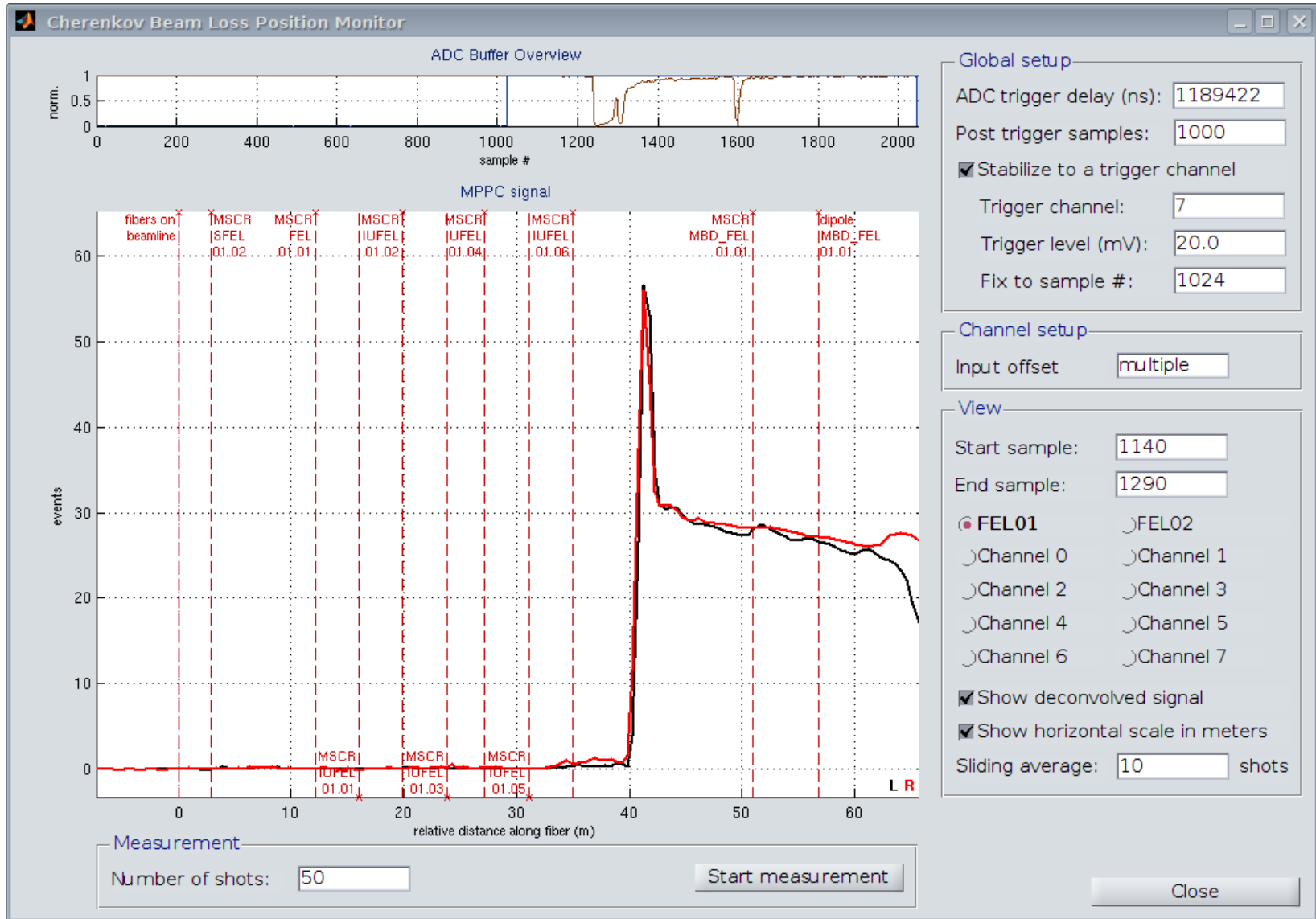
Undulator Cross Section



- Array of avalanche photodiodes (APDs) connected in parallel
- Reverse bias \rightarrow photon causes APD breakdown
- Photomultiplier-like gain
- Dynamic range limited by number of APDs
- Rise time: some 100 ps
- Hamamatsu S10362-11-050U:
400 APDs at ~ 70 V reverse bias



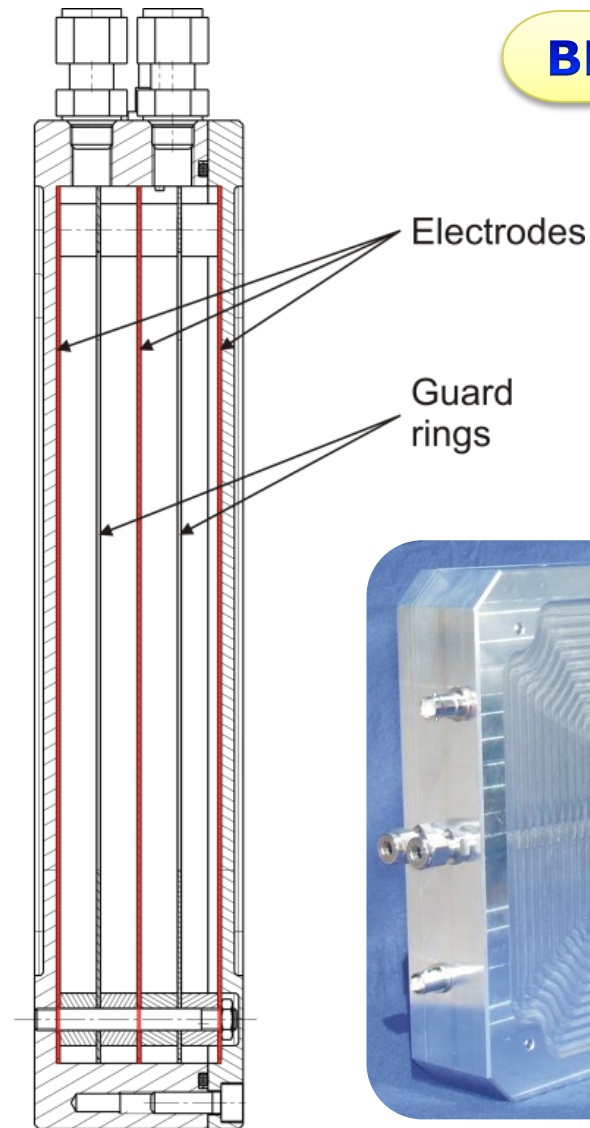


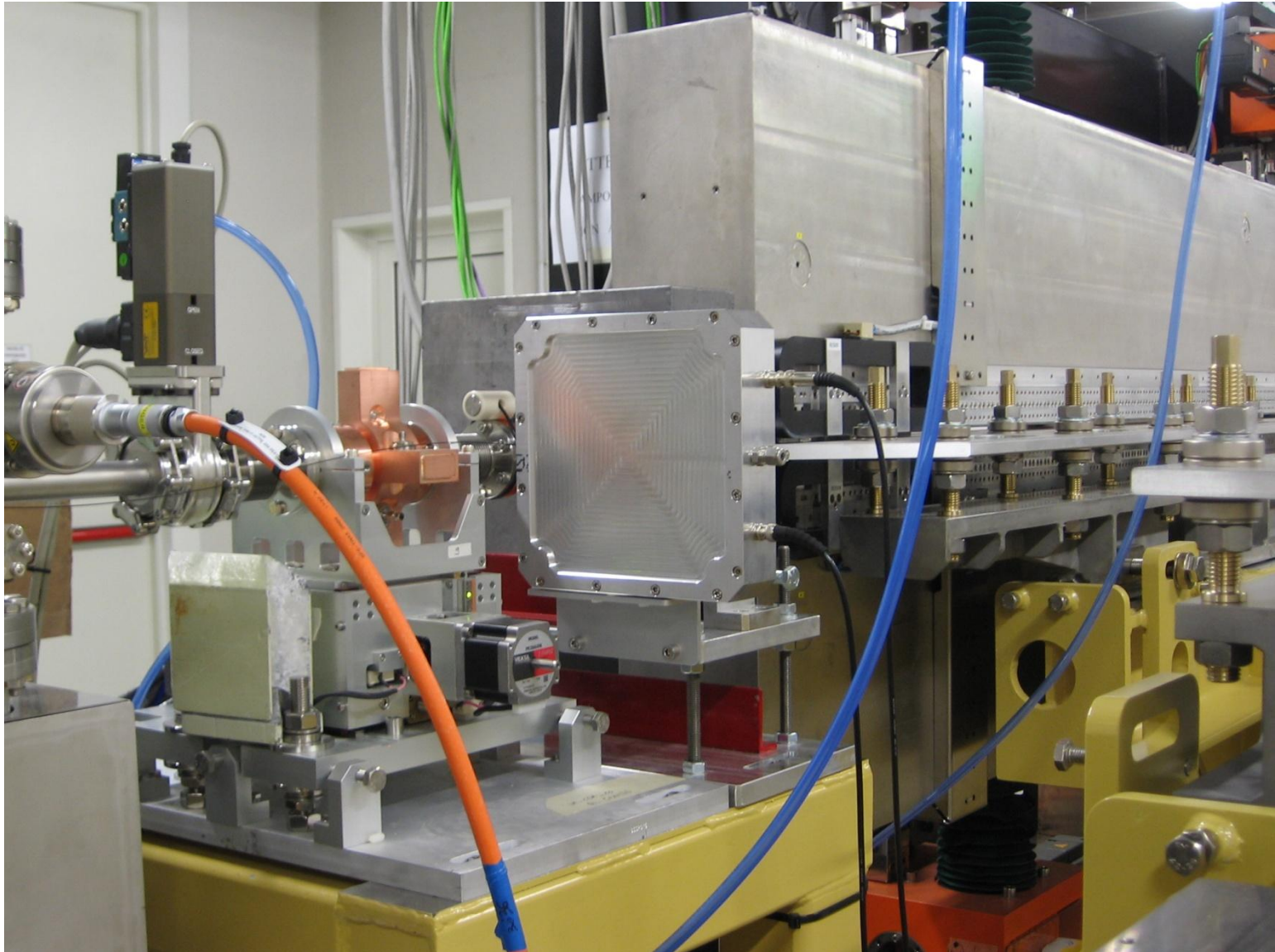


Ionization Chambers

- Milled aluminum enclosure
- Electrodes: printed circuit boards
- Use in air or with gas flux
- Volume:
1.3 l
- Voltage:
up to 1000 V
- Sensitivity (air):
 $\sim 46 \mu\text{C}/\text{Gy}$
- Leakage current:
 $\ll 200 \text{ fA}$ (at 1000 V)
- Fermi:
1 ionization chamber in air
per undulator segment (19 total)

BLM-IC02



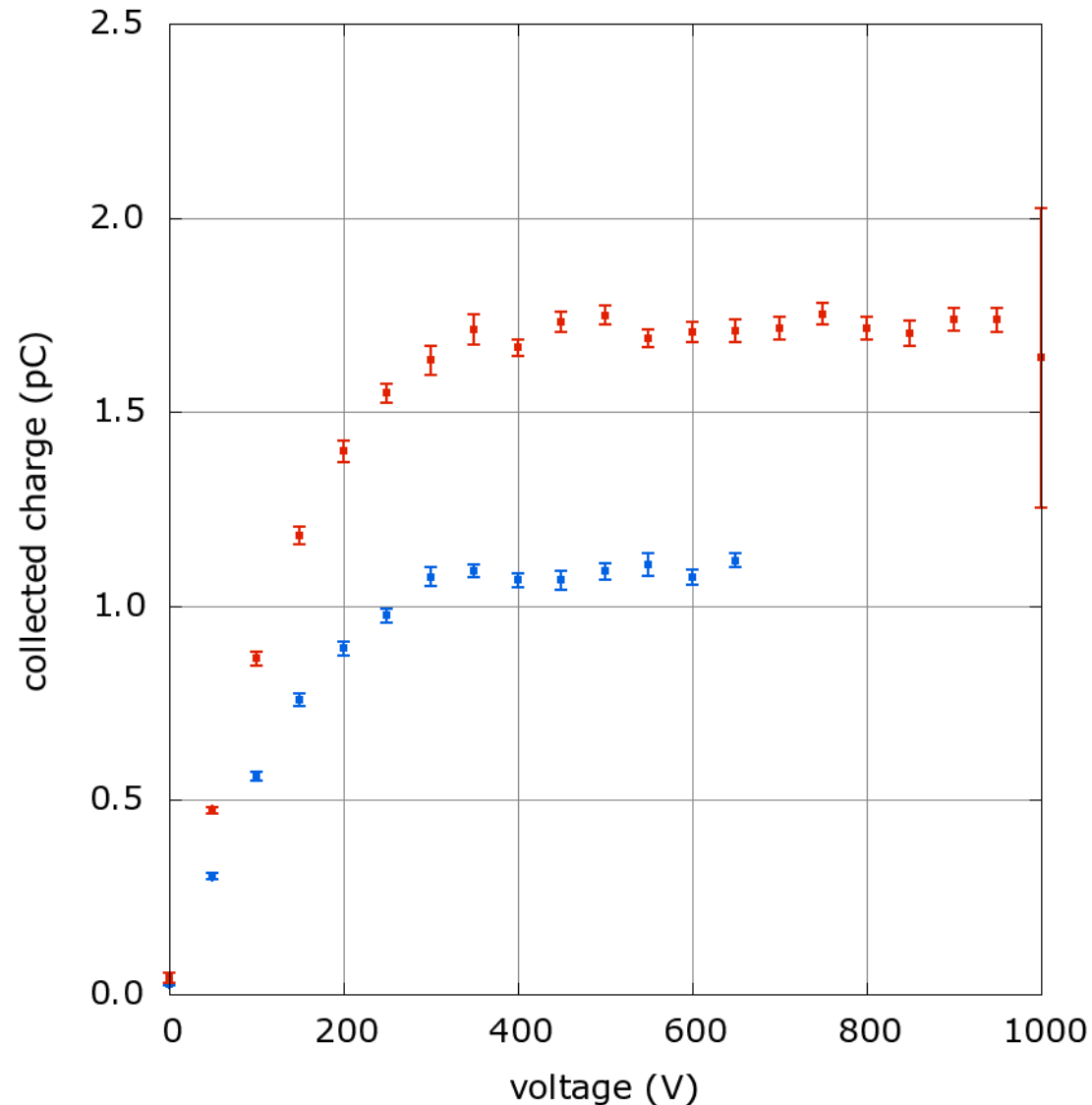


XPi DAS

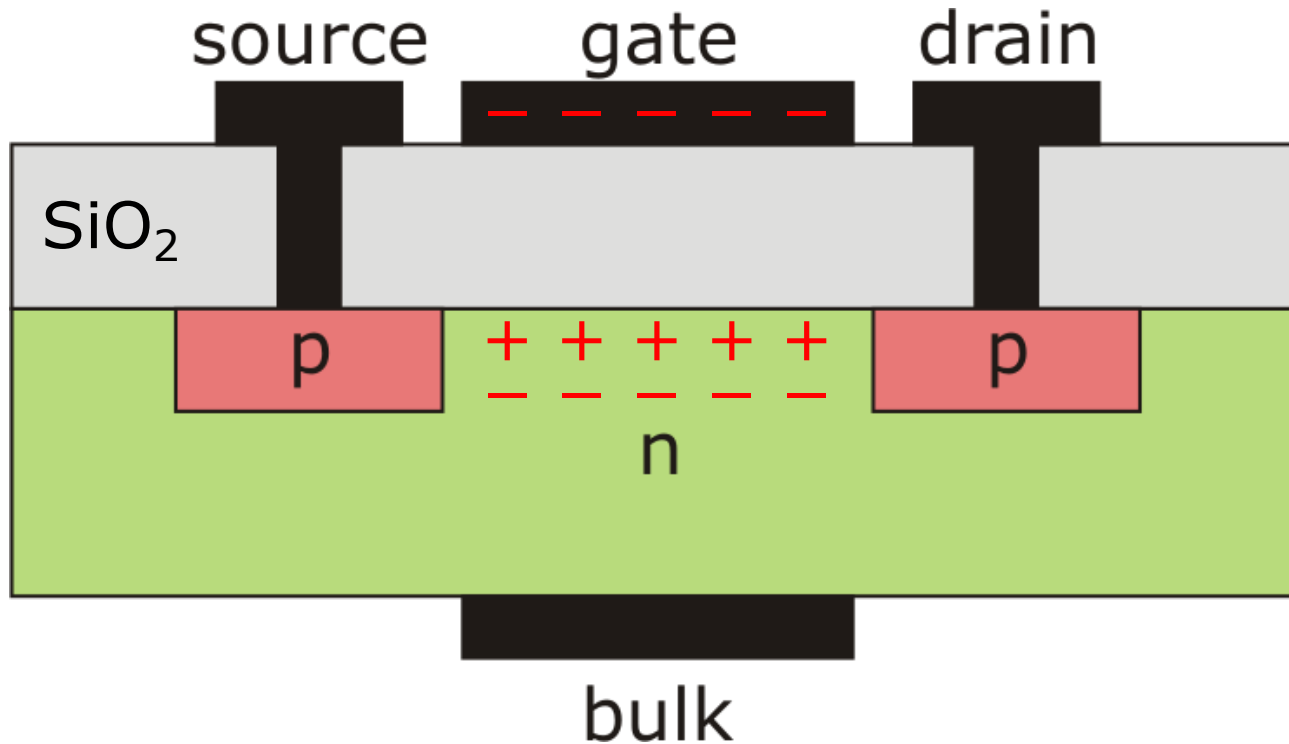
- Modular data acquisition system
- Ethernet interface
- 1× HV up to 2000 V, ≤ 1 W
- 4× Charge-integrating amplifier
 Ranges: 0...50 pC – 0...1.8 nC
 Integration time: 1 ms – 1 s
- 20-bit ADC
- Noise w/ Fermi chamber: $<0.4 \mu\text{Gy/h}$



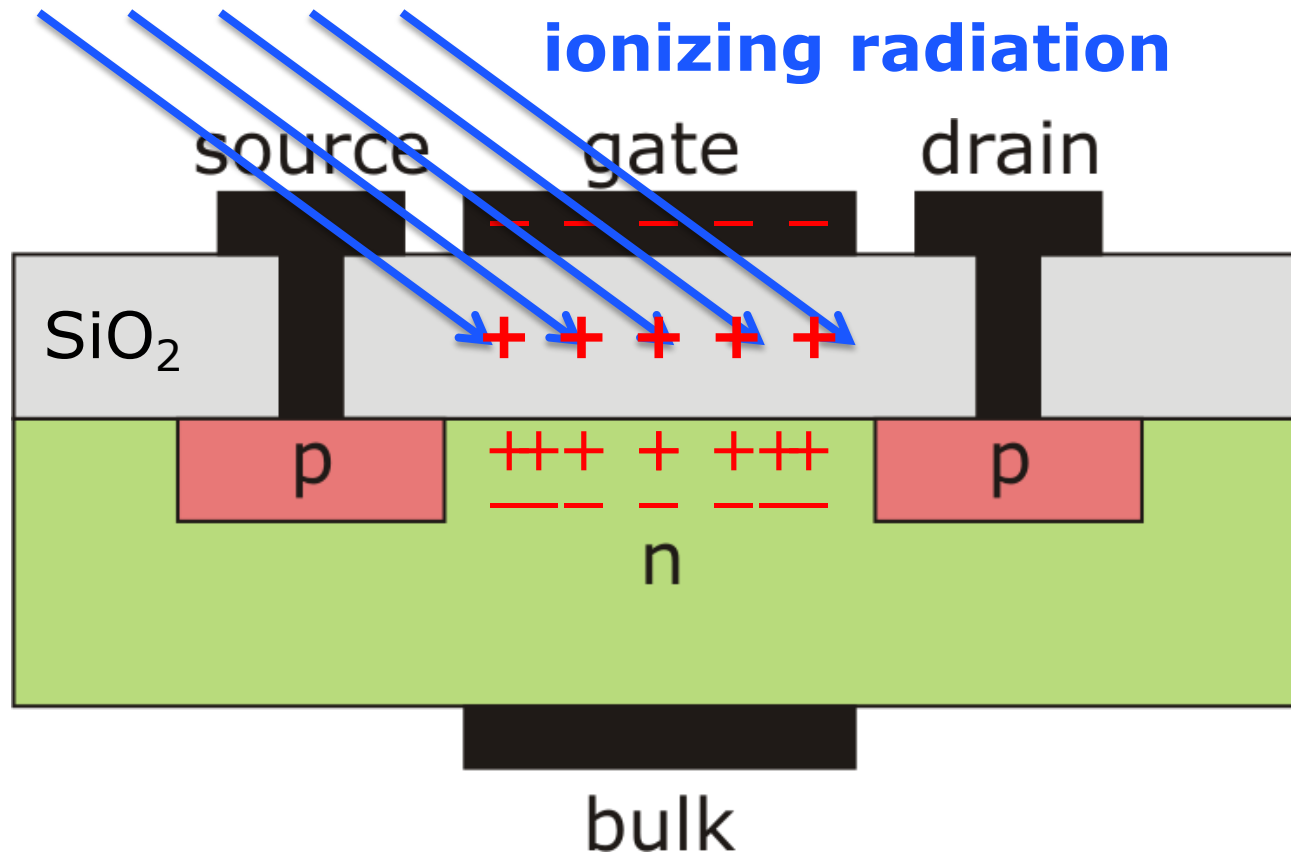
- Air filled chamber
- Charges collected:
 - Electrons
 - Oxygen ions (O_2^-)
 - Positive ions (N_2^+ etc.)
- Integration time: 3 ms (2 ms sufficient to collect all charges)



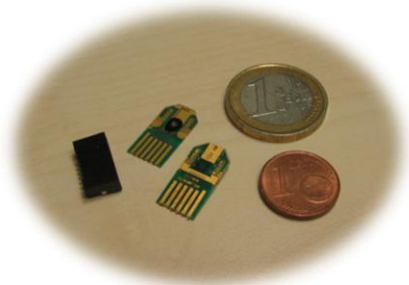
Online Solid-State Dosimetry



negative gate potential → conductive inversion layer

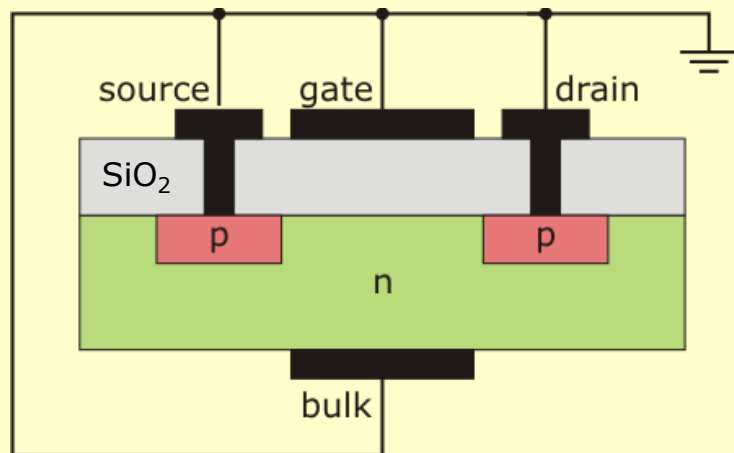


ionizing radiation → stationary charges in insulation layer

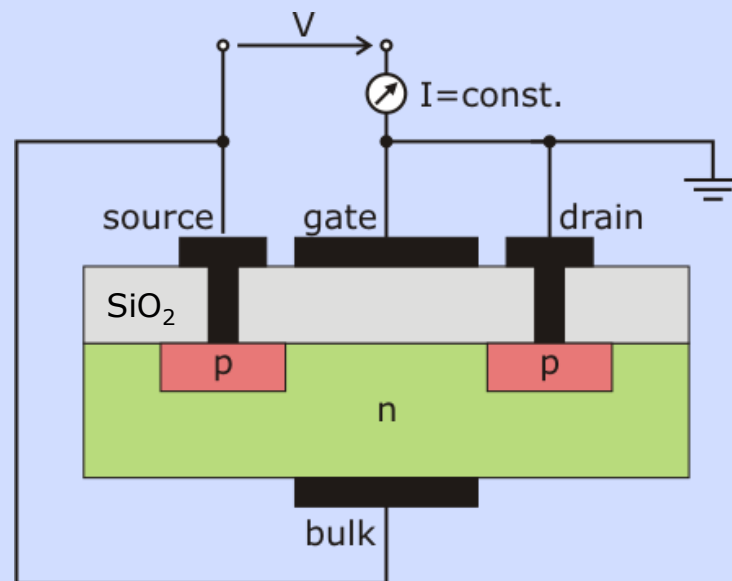


- REM Oxford Ltd. RADFET RFT-300-CC10G1
- Chip contains 2 p-channel MOSFETs with 300 nm insulator layer

exposure
"zero bias"



read-out



Track voltage for constant current (490 μ A) between source and drain

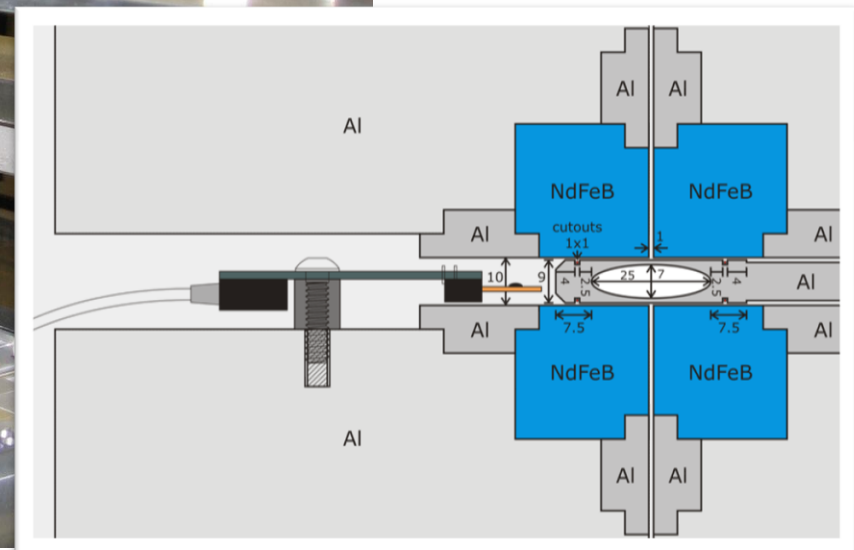
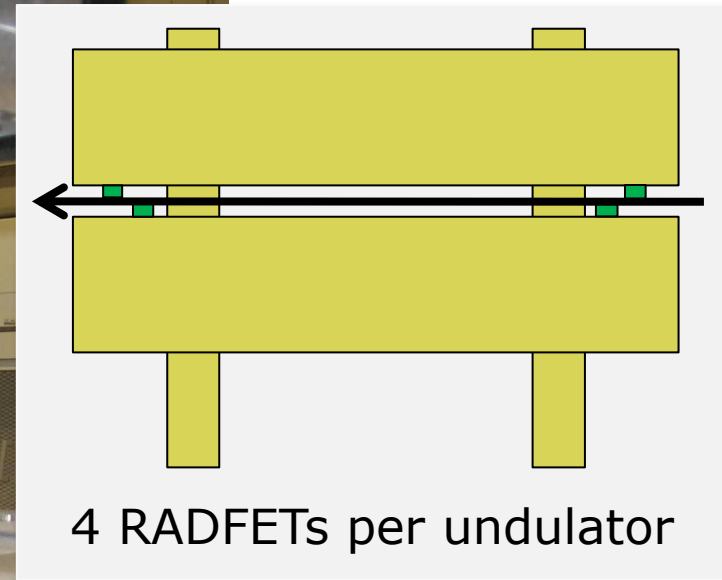
L01-DOSFET

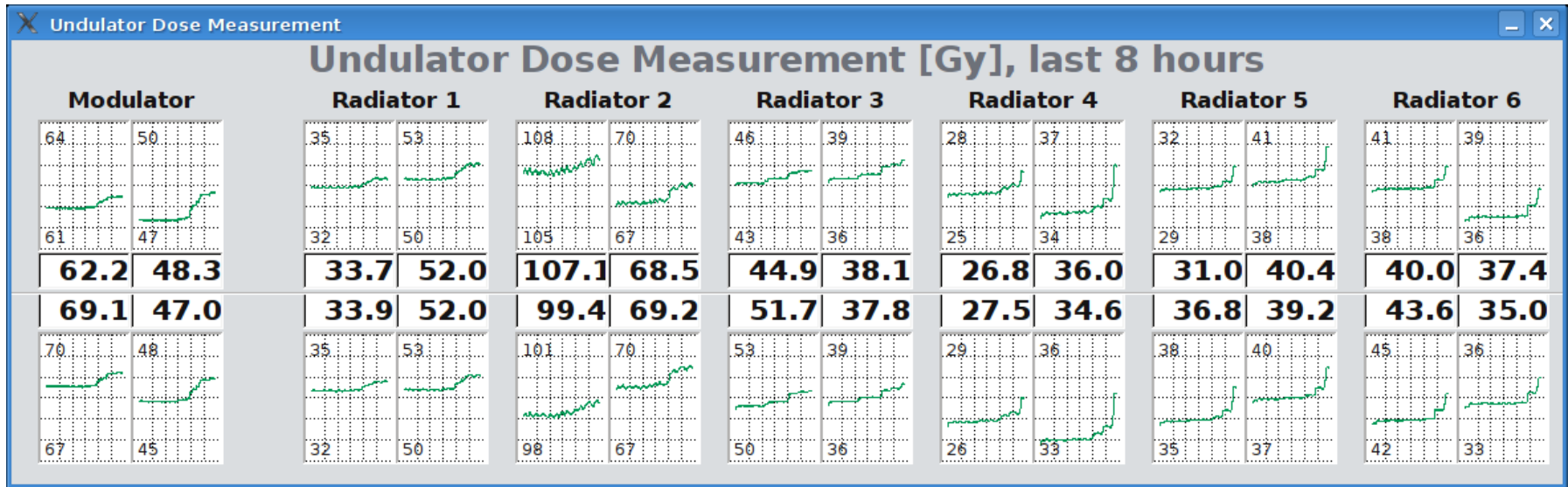
- Ethernet interface
- 4 RADFET channels
- Fixed read-out current: 490 μ A
- Voltage read-out: 24 bit ADC, up to 25 V
- Programmable interlock output
- Uses standard USB cables



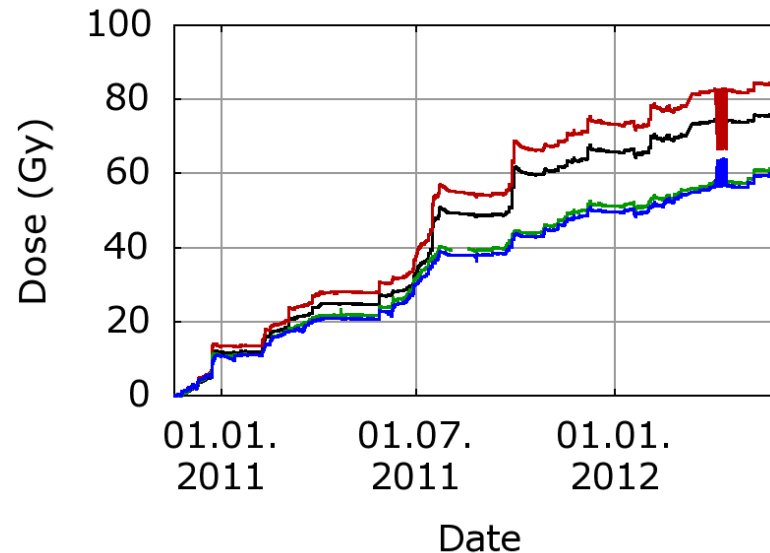
Photo: M. Peloi







First undulator
of FEL-1:



upstream bottom
upstream top
downstream top
downstream bottom

Thanks for your interest.

Many thanks to:

- Mario Ferianis, Alessandro Carniel, and the instrumentation and controls groups of Sincrotrone Trieste
- Arne Miller (Risø High Dose Reference Laboratory, DK)
- Andrew Holmes-Siedle (REM Oxford Ltd., UK)